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B1D05120K

MGT **A** Manufacturer Group of Technology

1200V 🛦 5A 🛦 SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type Excellent surge capability Easy paralleling due to positive V_F temperature coefficient TO-220-2L package ▲ Epoxy meets UL94-V0 Low forward voltage Temperature independent switching

SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	TJ	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V _{RRM}	1200V
Continuous Forward Current at T _c = 160°C	I _F	5A
Total Capacitive Charge (T, = 25°C)	Qc	32nC
Capacitance Stored Energy ($V_R = 800V$)	Ec	16µЈ
Diode Forward Voltage (T _J = 175°C, I _F = 5A)	V _F	1.78V
Power Dissipation	Ρ _{τοτ}	129W

RoHS

REACH

HALOGEN

FREE

APPLICATIONS

EV Charging	Industrial Inverters	Motors & Drives	Power Factor Correction	Renewable Energy	SMPS	UPS
∳∿⊧			PFC	*		

PIN DESCRIPTION

Circuit Diagram	Outline - Front View	Pin No.	Description
Case	Case	1	Cathode (Case Backside)
Case		2	Anode

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ABSOLUT MAXIMUM RATINGS **A** T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V _{RRM}	1200	V
Non-Repetitive Peak Reverse Voltage		V _{RSM}	1200	V
Continuous Forward Current	T _c = 25°C	I _F	30	А
Continuous Forward Current	T _C = 160°C	I _F	5	А
Non-Repetitive Forward Surge Current	T_{C} = 25°C, t_{p} = 10ms, Half Sine Wave	I _{FSM}	60	А
I ² t Value	T _c = 25°C, t _p = 10ms	∫i²dt	18	A ² s
Power Dissipation	T _C = 25°C	P _{TOT}	129	W
Power Dissipation	T _C = 110°C	P _{TOT}	56	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T _{STG}	-55 to +175	°C
TO-220 Mounting Torque	M3 Screw		0.7	Nm

ELECTRICAL CHARACTERISTICS

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	1200			V
Diode Forward Voltage	I _F = 5A, T _J = 25°C	V _F		1.40	1.60	V
Diode Forward Voltage	I _F = 5A, T _J = 175°C	V _F		1.78	2.30	V
Reverse Current	V _R = 1200V, T _J = 25°C	I _R		2	60	μΑ
Reverse Current	V _R = 1200V, T _J = 175°C	I _R		10	100	μA
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
	V _R = 800V, T _J = 25°C					
Total Capacitive Charge	$Q_C = \int_0^{V_R} C(V) dV$	Qc		32		nC
Total Capacitance	$V_{R} = 1V$, f = 1MHz, T _J = 25°C	С		352		рF
Total Capacitance	V_{R} = 400V, f = 1MHz, T _J = 25°C	С		31		рF
Total Capacitance	V _R = 800V, f = 1MHz, T _J = 25°C	С		23		pF
Capacitance Stored Energy	V _R = 800V, T _J = 25°C	Ec		16		μ

THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	R _{θ,JC}		1.16		K/W

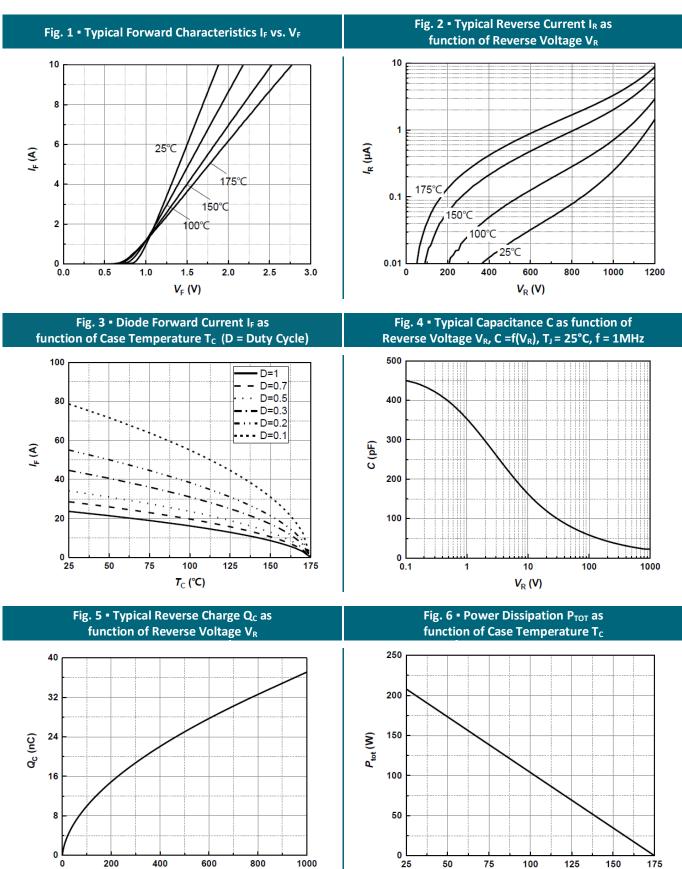


7_C (°C)

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REFERENCE DATA A TYPICAL PERFORMANCE



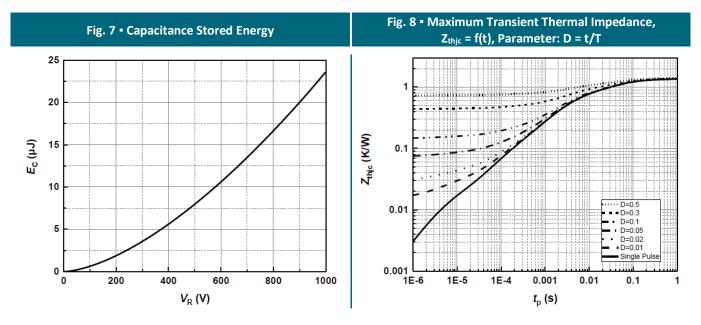
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*V*_R (V)



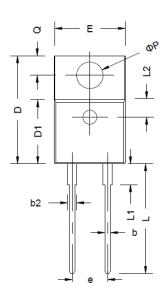
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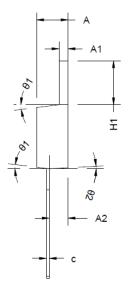
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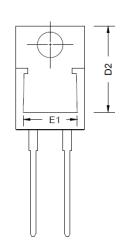




PACKAGE OUTLINE









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.37	4.57	4.77	E1	6.86	-	8.89
A1	1.22	-	1.40	е	4.98	5.08	5.18
A2	2.49	2.69	2.89	H1	6.10	6.30	6.50
b	0.75	-	0.96	L	12.70	-	13.70
b2	1.22	-	1.47	L1	-	-	4.10
С	0.30	-	0.48	L2		2.50 REF	
D	15.15	15.45	15.75	ØР	3.70	3.84	3.99
D1	9.05	9.15	9.25	Q	2.54	-	2.94
D2	11.40	-	12.88	θ1	5°	7°	9°
E	9.86	10.16	10.36	θ2	1°	3°	5°

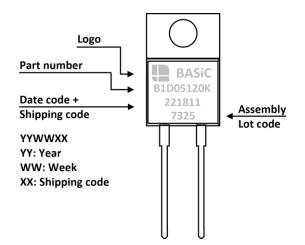
ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D05120K	TO-220-2L	Tube	50pcs	500pcs	5,000pcs

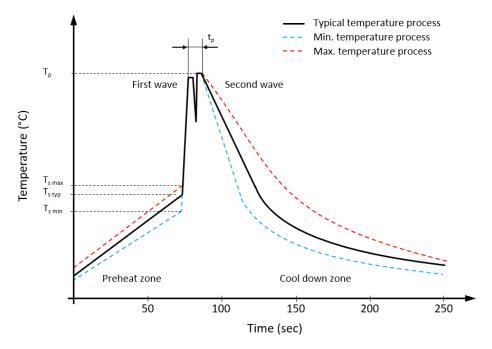


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PART MARKING



RECOMMENDED WAVE SOLDERING PROFILE ▲ THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value 🛦 Sn-Pb Assembly	Value 🔺 Pb-free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	$T_{s max}$	130 °C	130 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	70 seconds	70 seconds
Peak temperature	Τ _p	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes
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REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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